

isc Silicon PNP Power Transistor

2SB861

DESCRIPTION

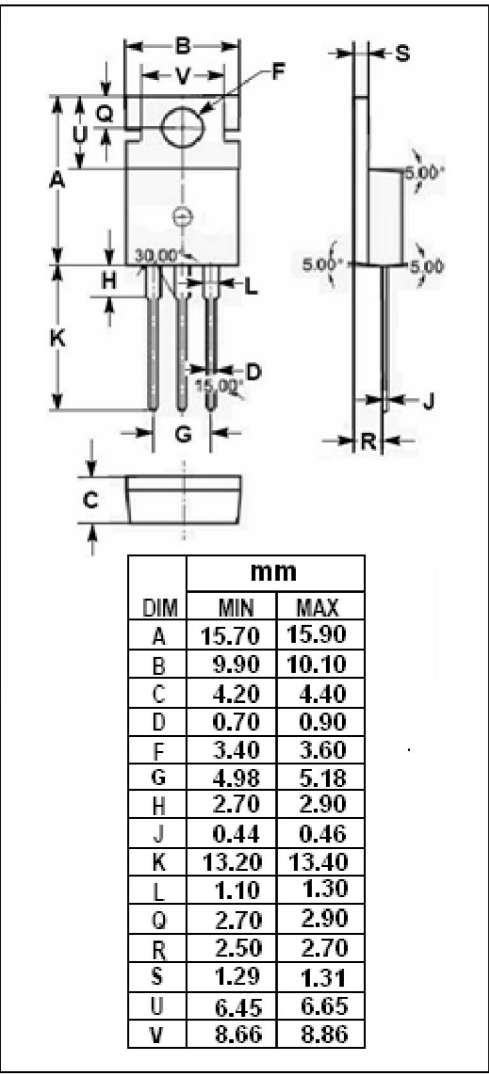
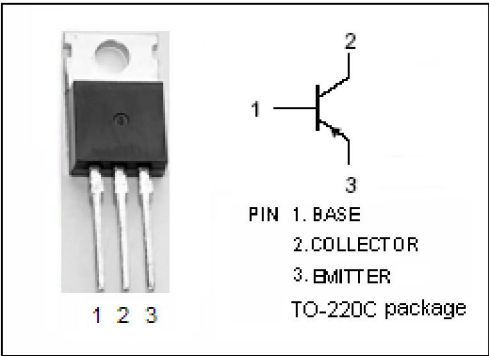
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min})$
- Wide Area of Safe Operation
- Complement to Type 2SD1138

APPLICATIONS

- Developed for low frequency power amplifier color TV vertical deflection output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	1.8	W
	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	30	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-45~150	$^{\circ}\text{C}$



isc Silicon PNP Power Transistor**2SB861****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA ; R _{BE} = ∞	-150			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA ; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -500mA ; I _B = -50mA			-3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -50mA ; V _{CE} = -4V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V ; I _E =0			-1	μ A
h _{FE-1}	DC Current Gain	I _C = -50mA ; V _{CE} = -4V	60		200	
h _{FE-2}	DC Current Gain	I _C = -500mA ; V _{CE} = -10V	60			
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} =-100V; f _{test} = 1.0MHz		30		pF

◆ h_{FE-1} Classifications

B	C
60-120	100-200

isc Silicon PNP Power Transistor

2SB861

